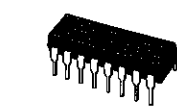


**DUAL 4-STAGE STATIC SHIFT REGISTER WITH SERIAL
INPUT/PARALLEL OUTPUT**

- MEDIUM SPEED OPERATION : 12MHz (typ.)
CLOCK RATE AT $V_{DD} - V_{SS} = 10V$
- FULLY STATIC OPERATION
- 8 MASTER-SLAVE FLIP-FLOPS PLUS INPUT
AND OUTPUT BUFFERING
- HIGH NOISE IMMUNITY
- QUIESCENT CURRENT SPECIFIED TO 20V
FOR HCC DEVICE
- INPUT CURRENT OF 100nA AT 18V AND 25°C
FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- 5V, 10V, AND 15V PARAMETRIC RATINGS
- MEETS ALL REQUIREMENTS OF JEDEC TEN-
TATIVE STANDARD N^o. 13A, "STANDARD
SPECIFICATIONS FOR DESCRIPTION OF "B"
SERIES CMOS DEVICES"



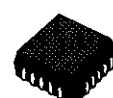
EY
(Plastic Package)



F
(Ceramic Frit Seal Package)



M1
(Micro Package)



C1
(Plastic Chip Carrier)

ORDER CODES :

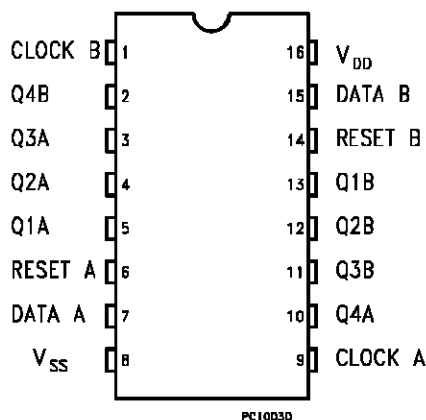
HCC4015BF	HCF4015BM1
HCF4015BEY	HCF4015BC1

DESCRIPTION

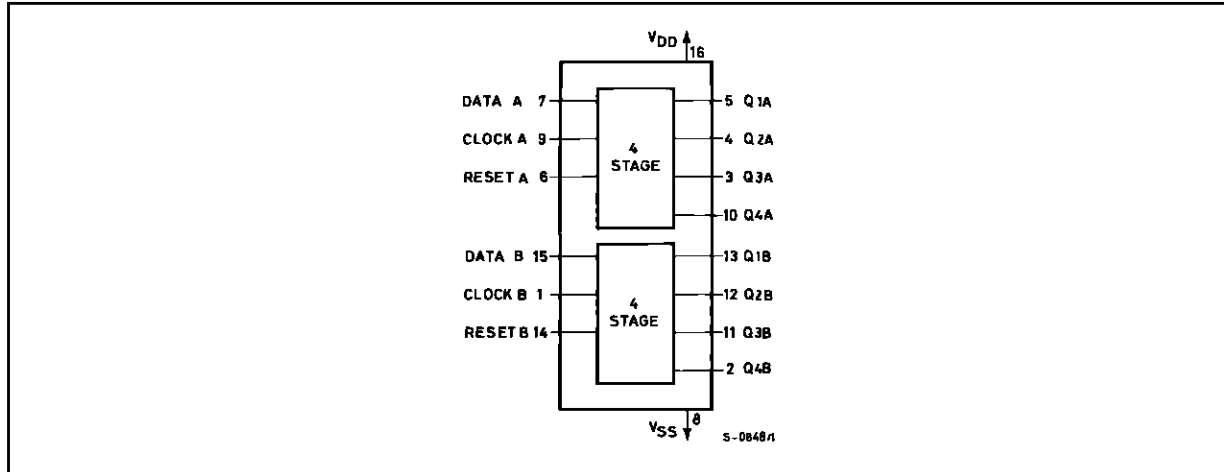
The **HCC4015B** (extended temperature range) and **HCF4015B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package and plastic micropackage.

The **HCC/HCF4015B** consists of two identical, independent, 4-stage serial-input/parallel-output registers. Each register has independent CLOCK and RESET inputs as well as a single serial DATA input. "Q" outputs are available from each of the four stages on both registers. All register stages are D-type, master-slave flip-flops. The logic level present at the DATA input is transferred into the first register stage and shifted over one stage at each positive-going clock transition. Resetting of all stages is accomplished by a high level on the reset line. Register expansion to 8 stages using one **HCC/HCF4015B** package, or to more than 8 stages using additional **HCC/HCF4015B**'s is possible.

PIN CONNECTIONS



FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage : HCC Types HCF Types	– 0.5 to + 20 – 0.5 to + 18	V V
V_i	Input Voltage	– 0.5 to $V_{DD} + 0.5$	V
I_i	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package)	200	mW
	Dissipation per Output Transistor for $T_{op} = \text{Full Package-temperature Range}$	100	mW
T_{op}	Operating Temperature : HCC Types HCF Types	– 55 to + 125 – 40 to + 85	°C °C
T_{stg}	Storage Temperature	– 65 to + 150	°C

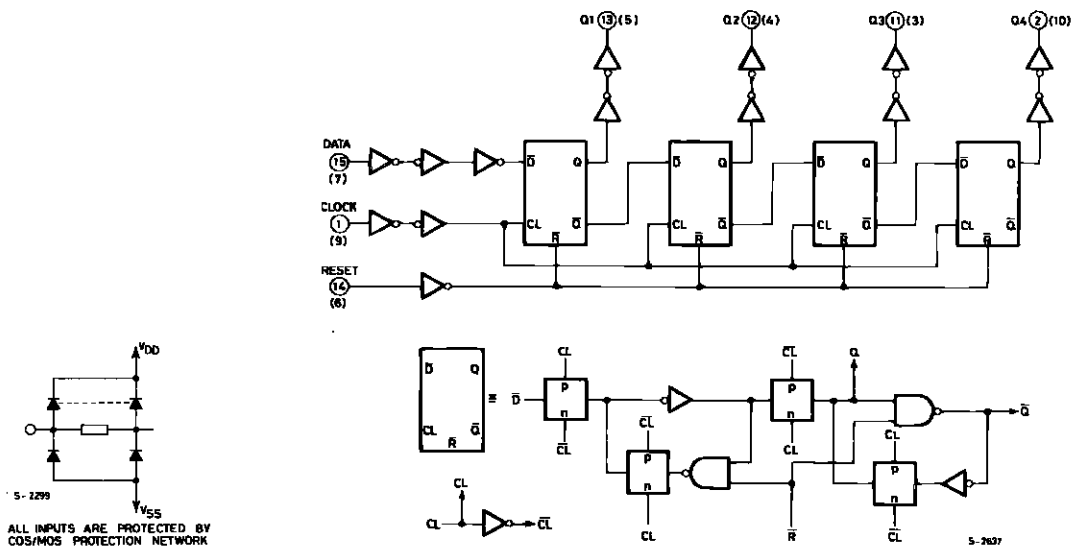
Stresses above those listed under "Absolute Maximum Ratings "may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V V
V_i	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature : HCC Types HCF Types	– 55 to + 125 – 40 to + 85	°C °C

LOGIC DIAGRAMS AND TRUTH TABLE



CL	D	R	Q_1	Q_n
$\overline{1}$	0	0	0	Q_{n-1}
$\overline{1}$	1	0	1	Q_{n-1}
$\overline{1}$	X	0	Q_1	Q_n (no. change)
X	X	1	0	0

STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value							Unit
			V _I (V)	V _O (V)	I _O (μA)	V _{DD} (V)	T _{Low} [*]		25° C			T _{High} [*]		
							Min.	Max.	Min.	Typ.	Max.	Min.	Max.	
I _L	Quiescent Current	HCC Types	0/ 5			5		5		0.04	5		150	μA
			0/10			10		10		0.04	10		300	
			0/15			15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	
		HCF Types	0/ 5			5		20		0.04	20		150	
			0/10			10		40		0.04	40		300	
			0/15			15		80		0.04	80		600	
V _{OH}	Output High Voltage	0/ 5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/ 5	2.5		5	– 2		– 1.6	– 3.2		– 1.15		mA
			0/ 5	4.6		5	– 0.64		– 0.51	– 1		– 0.36		
			0/10	9.5		10	– 1.6		– 1.3	– 2.6		– 0.9		
			0/15	13.5		15	– 4.2		– 3.4	– 6.8		– 2.4		
		HCF Types	0/ 5	2.5		5	– 1.53		– 1.36	– 3.2		– 1.1		
			0/ 5	4.6		5	– 0.52		– 0.44	– 1		– 0.36		
			0/10	9.5		10	– 1.3		– 1.1	– 2.6		– 0.9		
			0/15	13.5		15	– 3.6		– 3.0	– 6.8		– 2.4		
I _{OL}	Output Sink Current	HCC Types	0/ 5	0.4		5	0.64		0.51	1		0.36		mA
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/ 5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input	18		± 0.1		±10 ^{–5}	± 0.1		± 1	μA	
		HCF Types	0/15		15		± 0.3		±10 ^{–5}	± 0.3		± 1		
C _I	Input Capacitance			Any Input					5	7.5			pF	

* T_{Low}= - 55°C for **HCC** device : - 40°C for **HCF** device.

* T_{High}= + 125°C for **HCC** device : + 85°C for **HCF** device.

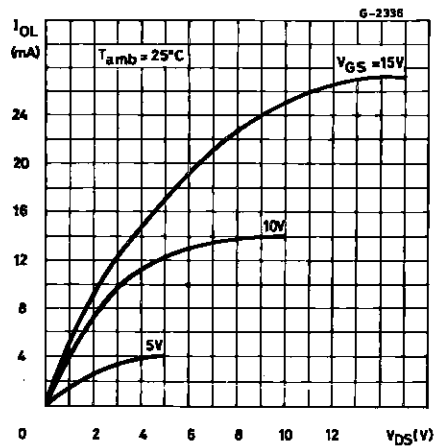
The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5 V min. with V_{DD} = 15V.

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\text{ }^{\circ}\text{C}$, all input rise and fall times = 20 ns)

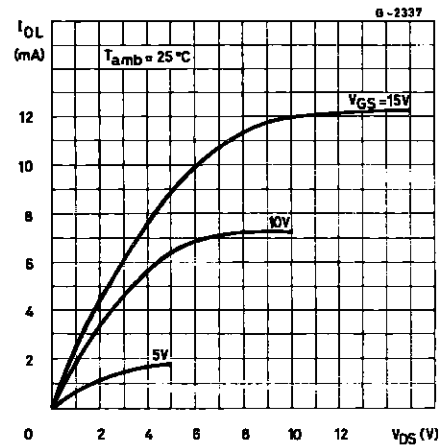
Symbol	Parameter	Test Conditions	Value				Unit
			V _{DD} (V)	Min.	Typ.	Max.	
CLOCKED OPERATION							
t _{PLH} , t _{PHL}	Propagation Delay Time (carry out or decoded out lines)		5		160	320	ns
			10		80	160	
			15		60	120	
t _{THL} , t _{TLH}	Transition Time (carry out or decoded out lines)		5		100	200	ns
			10		50	100	
			15		40	80	
f _{CL}	Maximum Clock Input Frequency		5	3	6		MHz
			10	6	12		
			15	8.5	17		
t _w	Clock Pulse Width		5	180	90		ns
			10	80	40		
			15	50	25		
t _r , t _f [*]	Clock Input Rise or Fall Time		5			15	μs
			10			15	
			15			15	
t _{setup}	Data Setup Time		5	70	35		ns
			10	40	20		
			15	30	15		
RESET OPERATION							
t _{PLH} , t _{PHL}	Propagation Delay Time		5		200	400	ns
			10		100	200	
			15		80	160	
t _w	Reset Pulse Width		5	200	100		ns
			10	80	40		
			15	60	30		

* If more than unit is cascaded in the parallel clocked application, t_{CL} should be made less than or equal to the sum of the fixed propagation delay at 15 pF and the transition time of the carry output driving stage for the estimated capacitive load.

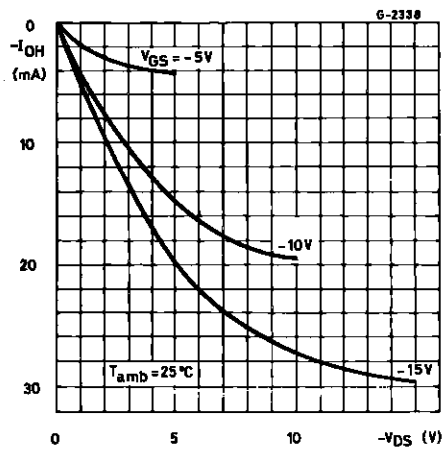
Typical Output Low (sink) Current Characteristics.



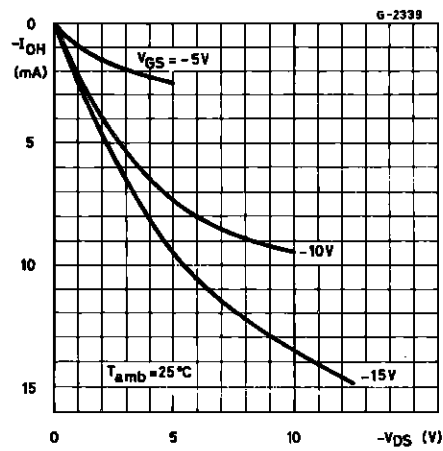
Minimum Output Low (sink) Current Characteristics.



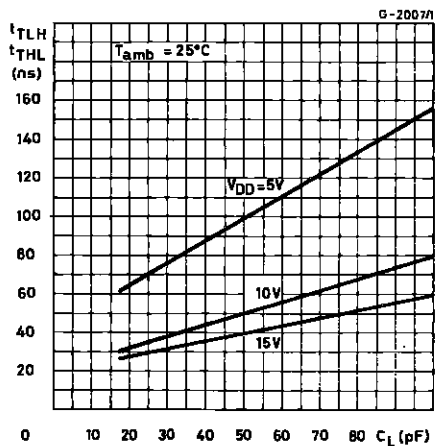
Typical Output High (source) Current Characteristics.



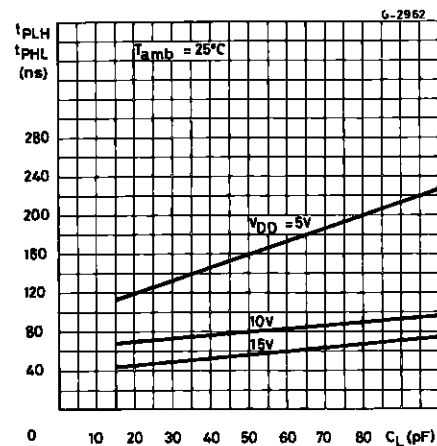
Minimum Output High (source) Current Characteristics.



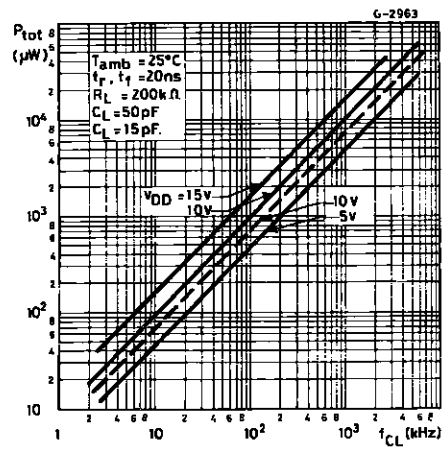
Typical transition Time vs. Load Capacitance.



Typical propagation Delay Time vs. Load Capacitance..

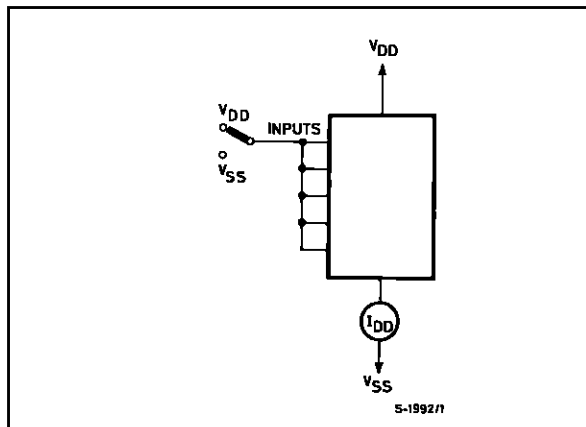


Typical Dynamic Power Dissipation vs. Frequency.

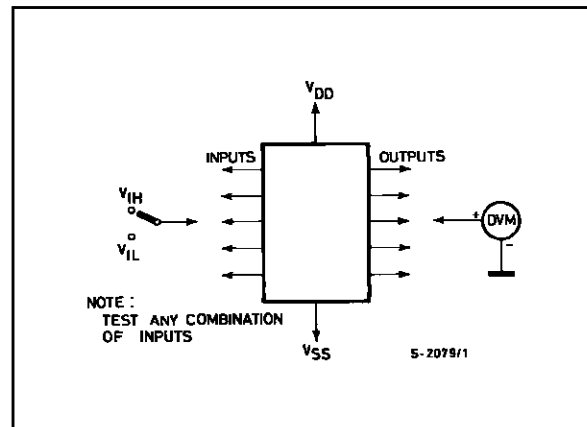


TEST CIRCUITS

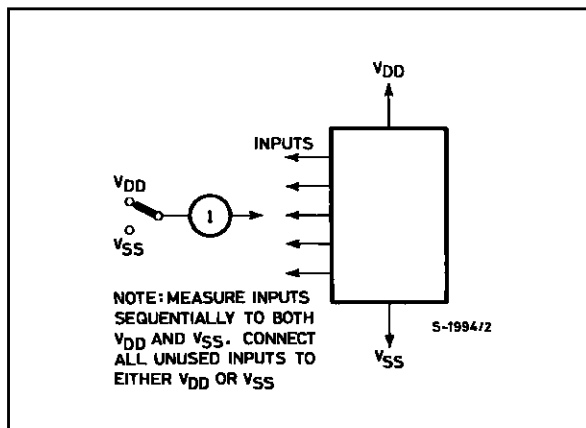
Quiescent Device Current



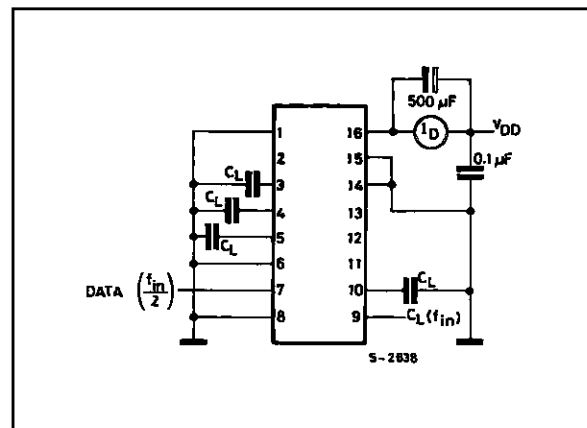
Input current.



Input Voltage.

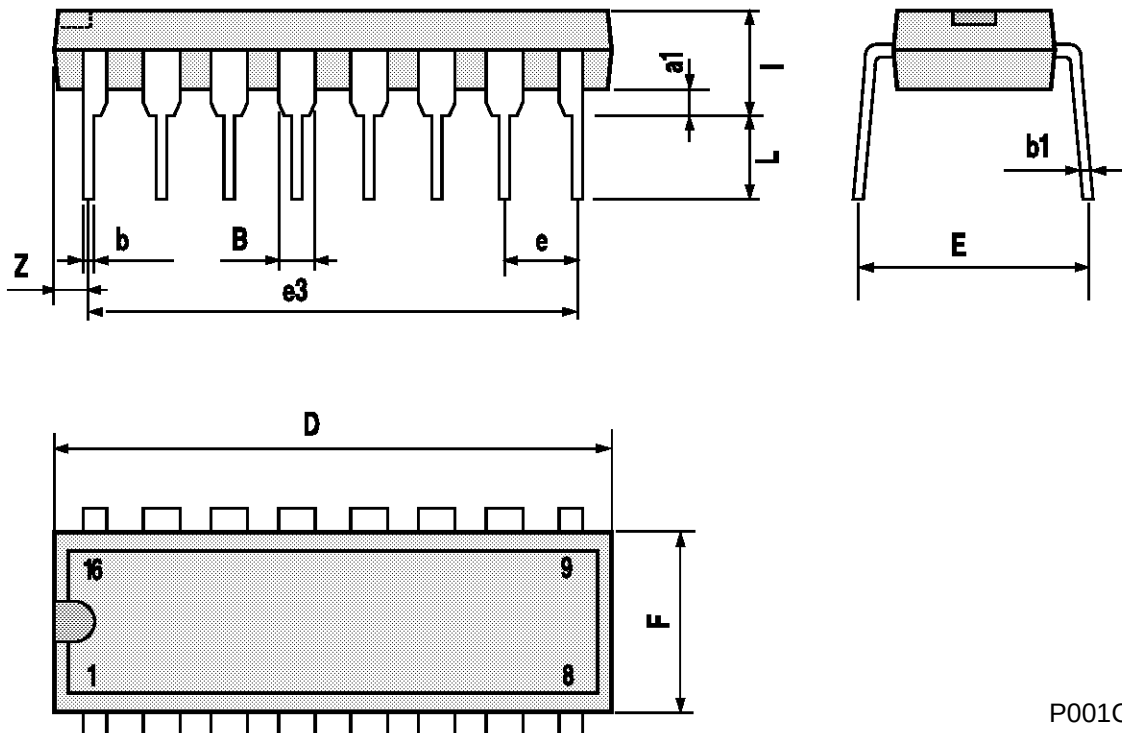


Power Dissipation.



Plastic DIP16 (0.25) MECHANICAL DATA

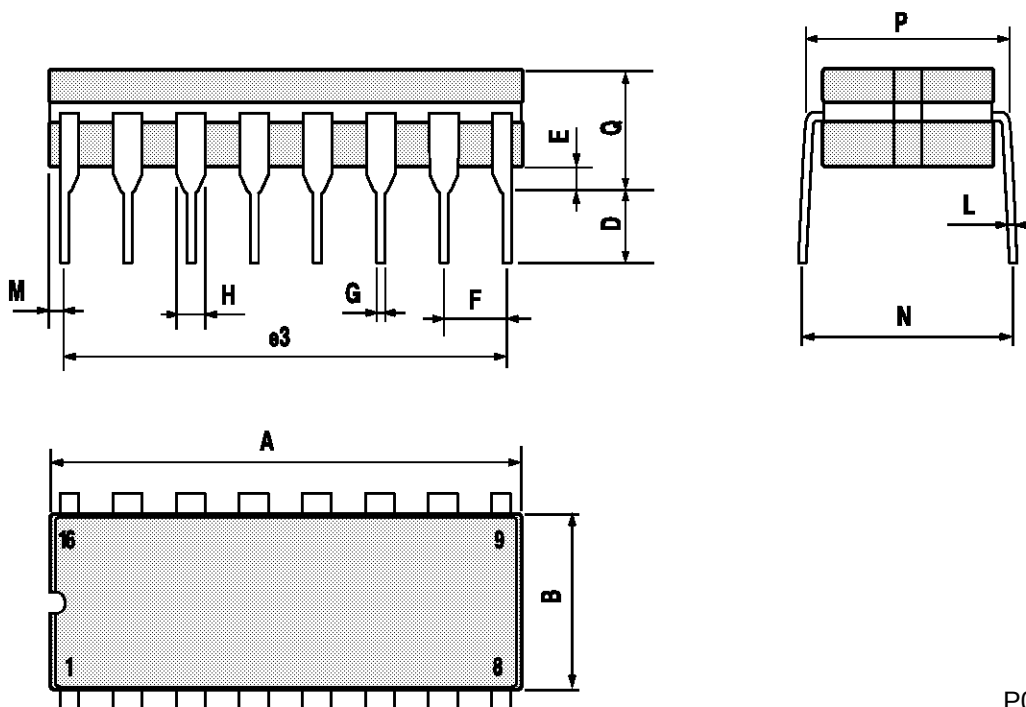
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



P001C

Ceramic DIP16/1 MECHANICAL DATA

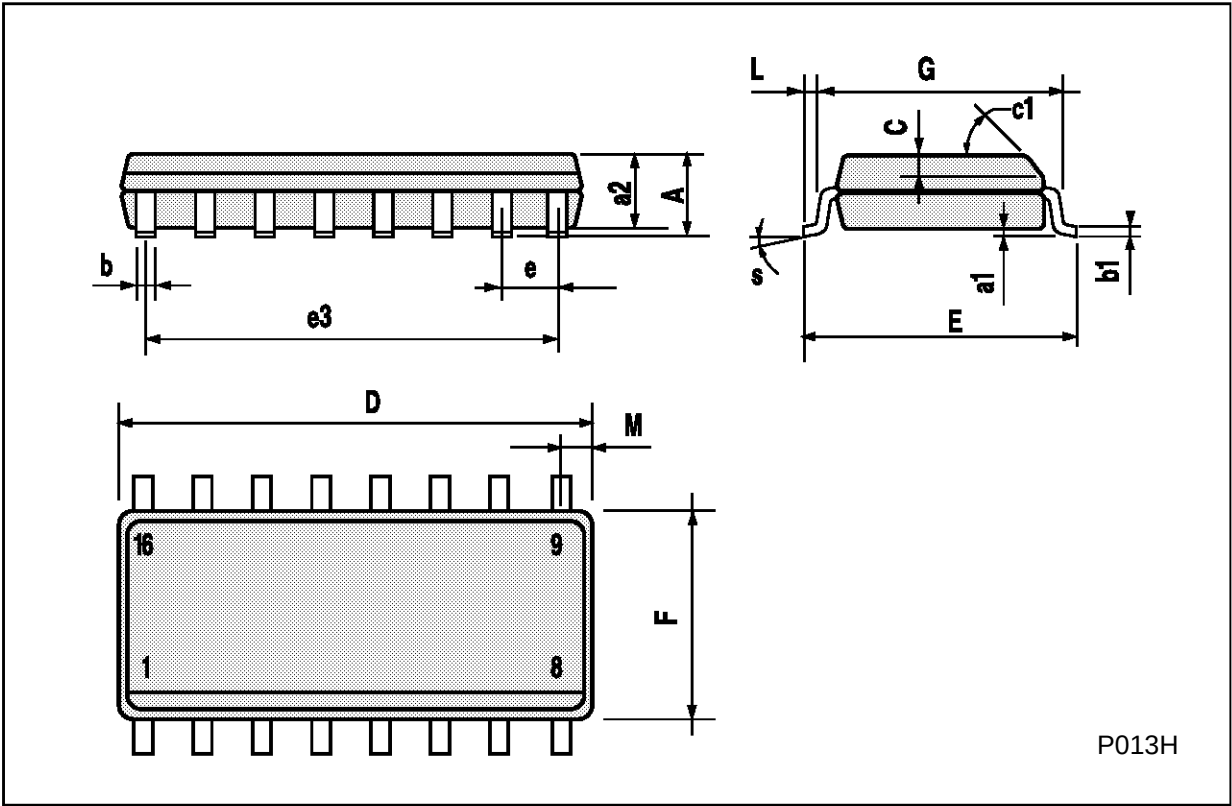
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			20			0.787
B			7			0.276
D		3.3			0.130	
E	0.38			0.015		
e3		17.78			0.700	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
H	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	0.51		1.27	0.020		0.050
N			10.3			0.406
P	7.8		8.05	0.307		0.317
Q			5.08			0.200



P053D

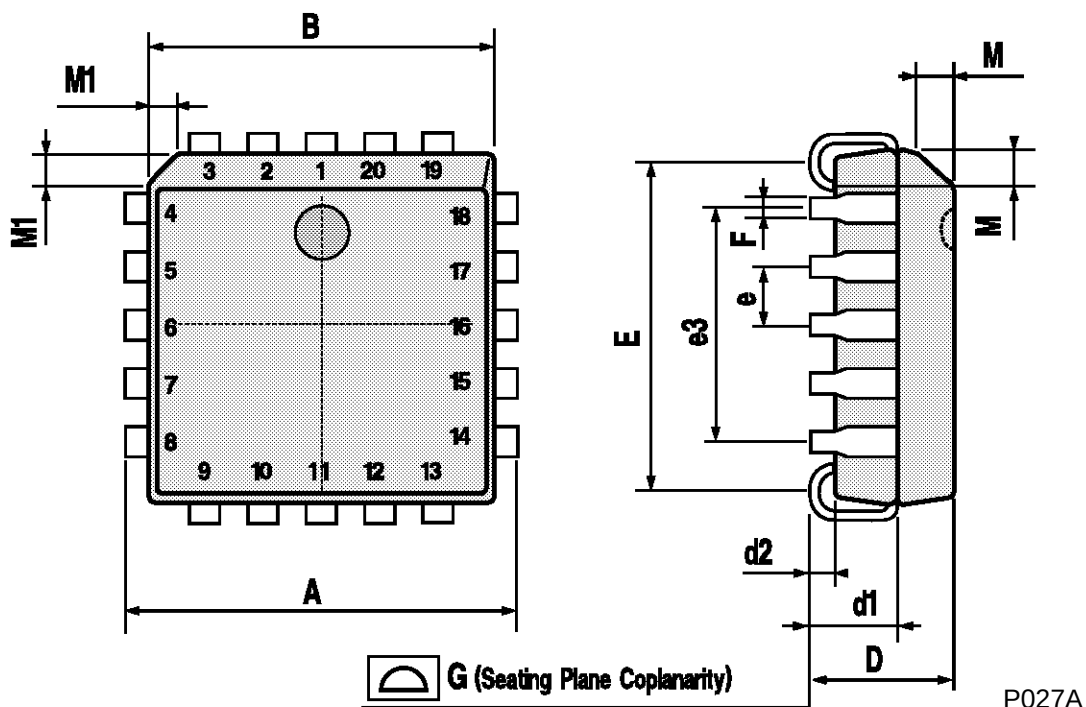
SO16 (Narrow) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.004		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	9.8		10	0.385		0.393
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.62			0.024
S	8° (max.)					



PLCC20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	9.78		10.03	0.385		0.395
B	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
e		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
M		1.27			0.050	
M1		1.14			0.045	



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